



65V PNP SMALL SIGNAL TRANSISTOR IN DFN1110-3/SWP

Description

The BC856BFHWQ bipolar junction transistor (BJT) is designed to meet the stringent requirements of automotive applications.

Features

- BVcEo > 65V
- I_C = 100mA High Continuous Collector Current
- Low-Profile, 0.6mm-High Package for Thin Applications
- Sidewall Tin Plating for Wettable Flanks in AOI
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The BC856BFHWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: U-DFN1110-3/SWP
- Package Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (23)
- Weight: 0.001714 grams (Approximate)

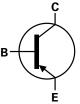
Application

Switching and amplification

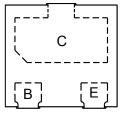
U-DFN1110-3/SWP (Type A)



Bottom View



Device Symbol



Top View Pin-Out

Ordering Information (Note 4)

Orderable Part Number	Package	Marking	Reel Size	Tape Width	Packing	
Orderable Part Number		war King	(inches)	(mm)	Qty.	Carrier
BC856BFHWQ-7	U-DFN1110-3/SWP (Type A)	4F	7	8	5,000	Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

U-DFN1110-3/SWP (Type A)



AB = Product type Marking Code YWW = Date Code Marking Y = Last Digit of Year (ex: 5 = 2025) WW = Week Code 01 to 53



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	Vcво	-80	V
Collector-Emitter Voltage	V _{CEO}	-65	V
Emitter-Base Voltage	V _{EBO}	-6	V
Continuous Collector Current	Ic	-100	mA
Peak Pulse Collector Current	I _{CM}	-200	mA
Peak Base Current	Івм	-100	mA

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 5)	PD	420	mW
Thermal Resistance, Junction to Ambient	(Note 5)	Reja	298	°C/W
Thermal Resistance, Junction to Case	(Note 6)	Rejc	109	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge – Charged Device Model	ESD CDM	1000	V	C3

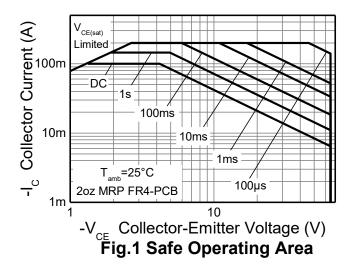
Notes:

^{5.} For a device mounted with the exposed collector pads on minimum recommended pad layout that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

^{6.} Thermal resistance from junction to the top of the case 7. Refer to JEDEC specification JESD22-A114 and JESD22-C101.



Thermal Characteristics and Derating Information



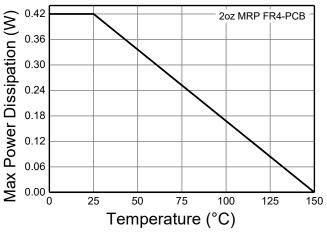


Fig.2 Derating Curve

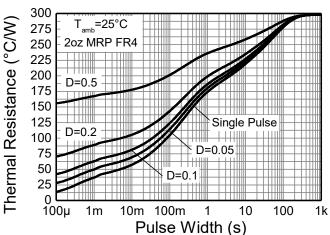


Fig.3 Transient Thermal Impedance

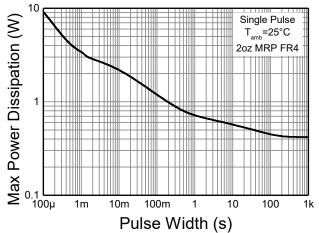


Fig.4 Pulse Power Dissipation



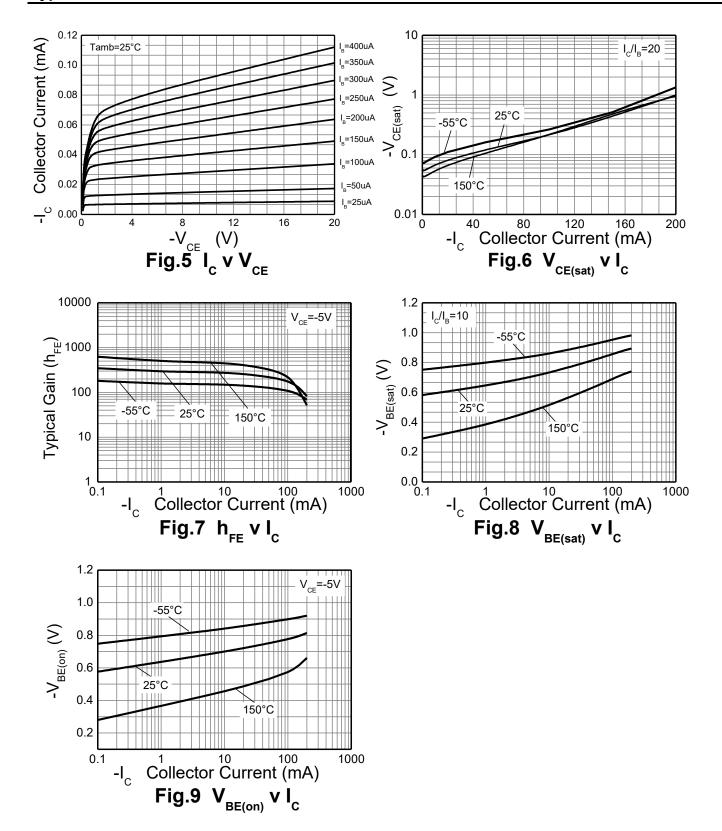
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV _{CBO}	-80			V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 8)	BVceo	-65			V	I _C = -10mA
Emitter-Base Breakdown Voltage	BVEBO	-7	_	_	V	I _E = -100μA
Collector-Base Cutoff Current	lone			-15	nA	V _{CB} = -30V, I _E = 0
Collector-base Cuton Current	Ісво	_	_	-5	μA	V _{CB} = -30V, I _E = 0, T _A = +150°C
Emitter-Base Cutoff Current	I _{EBO}	_	_	-100	nA	$V_{EB} = -5.6V, I_{C} = 0$
DC Current Gain	hfE	220	_	475	_	V _{CE} = -5V, I _C = -2mA
Oallanten Freitten Oatsmatien Walten (Nate O)	VCE(sat)	_	_	-300	mV l	$I_C = -10$ mA, $I_B = -0.5$ mA
Collector-Emitter Saturation Voltage (Note 8)		_	_	-650		I _C = -100mA, I _B = -5mA
Daga Emitter Turn on Voltage (Note 9)	V _{BE(on)}	-600	_	-750	mv	V _{CE} = -5V, I _C = -2mA
Base-Emitter Turn-on Voltage (Note 8)		_	_	-820		V _{CE} = -5V, I _C = -10mA
Dage Emitter Seturation Valtage (Note 9)	V _{BE} (sat)	_	-700	_	V	$I_C = -10mA$, $I_B = -0.5mA$
Base-Emitter Saturation Voltage (Note 8)		_	-850	_		I _C = -100mA, I _B = -5mA
Transition Frequency	f⊤	100			MHz	$V_{CE} = -5V, I_{C} = -10mA,$ f = 100MHz
Output (Collector) Capacitance	Cobc	_	2	_	pF	V _{CB} = -10V, f = 1MHz
Output (Emitter) Capacitance	Coec		10		pF	V _{EB} = -0.5V, f = 1MHz
Noise Figure	NF	_	_	10	dB	V_{CE} = -5V, Ic = -200μA, R _S = 2kΩ, f = 1kHz BW=200Hz

Note: 8. Measured under pulsed conditions. Pulse width $\leq 300 \mu s$. Duty cycle $\leq 2\%$.



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

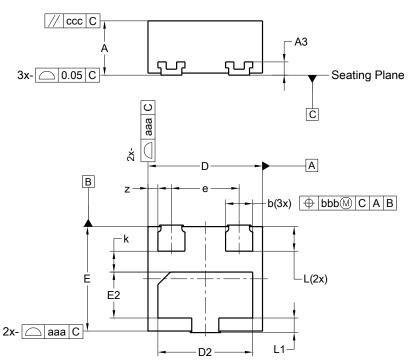




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN1110-3/SWP (Type A)



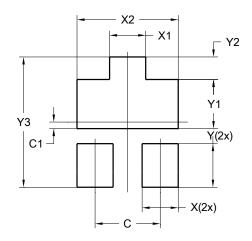
U-DFN1110-3/SWP (Type A)					
Dim	Min Max Typ				
Α	0.47	0.57	0.52		
A1	0.00	0.05	0.03		
A3	_	_	0.127		
b	0.22	0.30	0.26		
D	1.05	1.15	1.10		
D2	0.87	0.95	0.91		
е	0	.65 BS	\circ		
Е	0.95	1.05	1.00		
E2	0.40	0.48	0.44		
k	_	-	0.20		
٦	0.20	0.27	0.23		
L1	0.09	0.19	0.14		
Z	0.095				
aaa	0.25				
bbb	0.10				
CCC	0.10				
All Dimensions in mm					

Note: Side wall tin plated package for wettable flanks in AOI.

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN1110-3/SWP (Type A)



Dimensions	Value		
Dilliensions	(in mm)		
С	0.650		
C1	0.065		
X	0.360		
X1	0.360		
X2	1.010		
Y	0.435		
Y1	0.490		
Y2	0.225		
Y3	1.300		



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